

BIPOLAR ANALOG INTEGRATED CIRCUIT

μ PC1658G

LOW NOISE, HIGH FREQUENCY Si MMIC AMPLIFIER

DESCRIPTION

The μ PC1658G is a silicon monolithic integrated circuit designed as amplifier for high frequency system applications. Bandwidth and output power level can be determined according to external resistor constants of negative feedback and final stage collector. This IC is available in 8-pin plastic SOP.

This IC is manufactured using NEC's 10 GHz fr NESAT™ II silicon bipolar process. This process uses silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion/migration. Thus, this IC has excellent performance, uniformity and reliability.

FEATURES

- Low noise figure : $NF \leq 3$ dB
- Due to the external negative feedback circuit, the power gain can be adjustable by selecting appropriate resistance constants.
 - : $G_P \geq 40$ dB @ Without negative feedback resistor
 - : $G_P \geq 18$ dB @ With negative feedback resistor
- Wideband response : $f_{3dB} = 1.0$ GHz @ $G_P = 18$ dB
- External resistor can vary the collector current of the final transistor in the IC to adjust the saturated output level.

APPLICATIONS

- IF buffer amplifier of high frequency system
- Measurement equipment

ORDERING INFORMATION

| Part Number | Package | Marking | Supplying Form |
|------------------|-----------------------------|---------|--|
| μ PC1658G-E1 | 8-pin plastic SOP (225 mil) | 1658 | Embossed tape 12 mm wide. 1 pin is tape pull-out direction. Qty 2.5 kp/reel. |

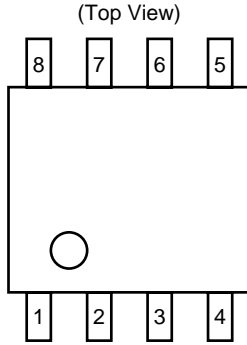
Remark To order evaluation samples, please contact your local NEC sales office.
(Part number for sample order: μ PC1658G)

Caution TO-99 CAN package (μ PC1658A) and 8-pin plastic DIP package (μ PC1658C) products are discontinued.

Caution Electro-static sensitive devices

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

PIN CONNECTIONS



| Pin No. | Pin Name |
|---------|-----------------|
| 1 | GND |
| 2 | Test Point |
| 3 | Output |
| 4 | V _{cc} |
| 5 | Test Point |
| 6 | Input |
| 7 | Bypass |
| 8 | Bypass |

PIN EXPLANATION

| Pin No. | Pin Name | Function and Applications | Internal Equivalent Circuit |
|---------|-----------------|--|-----------------------------|
| 1 | GND | Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as possible. All the ground pins must be connected together with wide ground pattern to decrease impedance difference. | |
| 2 | Test Point | Test Point pin. The collector current of Q ₂ and Q ₃ can be varied by connecting an appropriate external resistance between this pin and GND or by shorting this pin to GND. By increasing the collector current of Q ₃ , the output level improves and the IC can operate as a low-distortion amplifier. | |
| 3 | Output | Signal output pin. This pin must be coupled to signal source with capacitor for DC cut. | |
| 4 | V _{cc} | Power supply pin. This pin should be externally equipped with bypass capacitor to minimize its impedance. | |
| 5 | Test Point | By connecting this pin to the power supply through an appropriate external resistance or by shorting this pin directly to the power supply, the gain can be adjustable (when using pin 2, short the pin 5 to the power supply). | |
| 6 | Input | Signal input pin. Through negative feedback from output pin with an external circuit, the IC operates as a wideband amplifier. | |
| 7 | Bypass | Emitter bypass pins of Q ₁ . Bypass these pins to GND with a capacitor. | |
| 8 | Bypass | | |

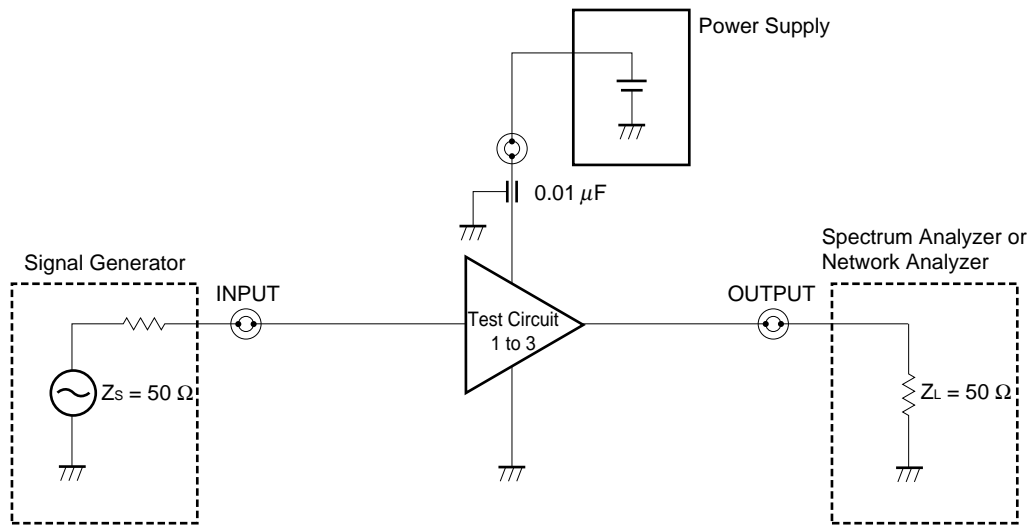
ABSOLUTE MAXIMUM RATINGS

| Parameter | Symbol | Conditions | Rating | Unit |
|-------------------------------|------------------|--|-------------|------|
| Supply Voltage | V _{CC} | T _A = +25 °C | 12 | V |
| Output Transistor Current | I _{O3} | T _A = +25 °C | 40 | mA |
| Power Dissipation | P _D | Mounted on double copper clad 50 × 50 × 1.6 mm epoxy glass PWB (T _A = +70 °C) | 280 | mW |
| Operating Ambient Temperature | T _A | | -40 to +75 | °C |
| Storage Temperature | T _{stg} | | -55 to +150 | °C |

ELECTRICAL CHARACTERISTICS (T_A = +25 °C, V_{CC} = 10.0 V, Z_S = Z_L = 50 Ω, Test circuit 1)

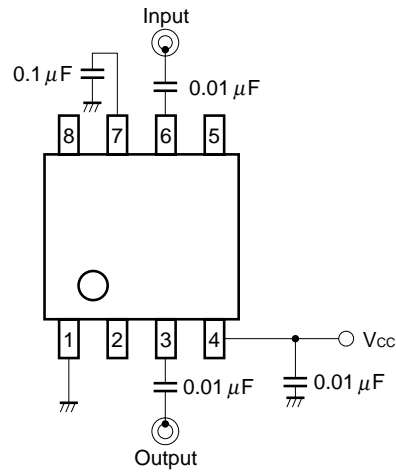
| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|-----------------|-----------------|-------------|------|------|------|------|
| Circuit Current | I _{CC} | No signal | 9 | - | 18 | mA |
| Power Gain 1 | G _{P1} | f = 10 MHz | 37 | 41 | 45 | dB |
| Power Gain 2 | G _{P2} | f = 100 MHz | 28 | 31 | 34 | dB |
| Power Gain 3 | G _{P3} | f = 500 MHz | 14 | 17 | 20 | dB |
| Noise Figure 1 | NF ₁ | f = 100 MHz | - | 1.5 | 2.5 | dB |
| Noise Figure 2 | NF ₂ | f = 500 MHz | - | 2.0 | 3.0 | dB |

TEST SET-UP

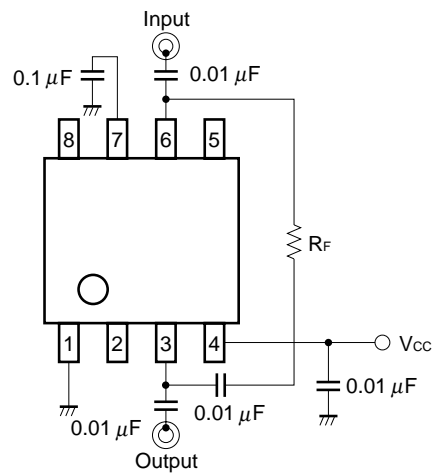


TEST CIRCUITS

TEST CIRCUIT 1 (Low-noise amplifier)



TEST CIRCUIT 2 (Wideband low-noise amplifier)



TEST CIRCUIT 3 (Wideband low-noise amplifier with improved output level)

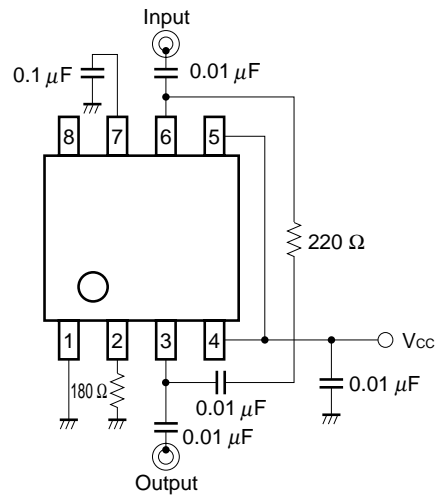
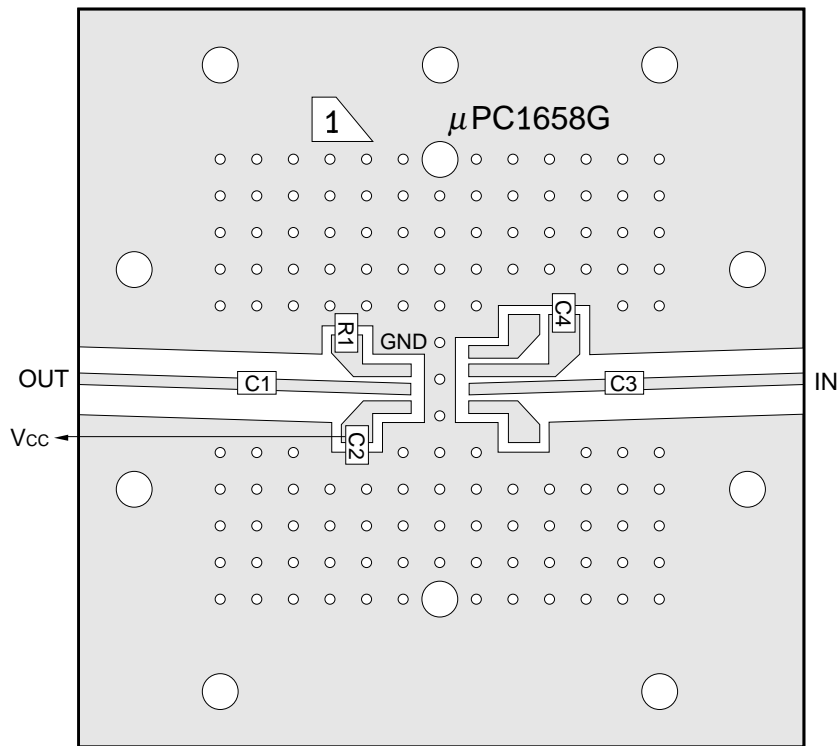


ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



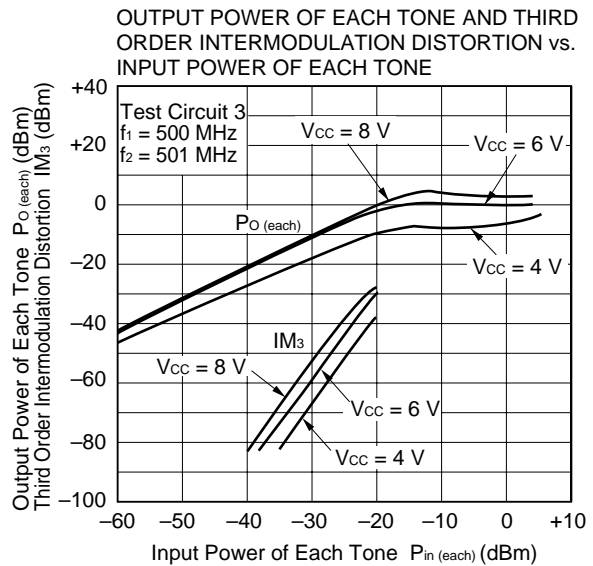
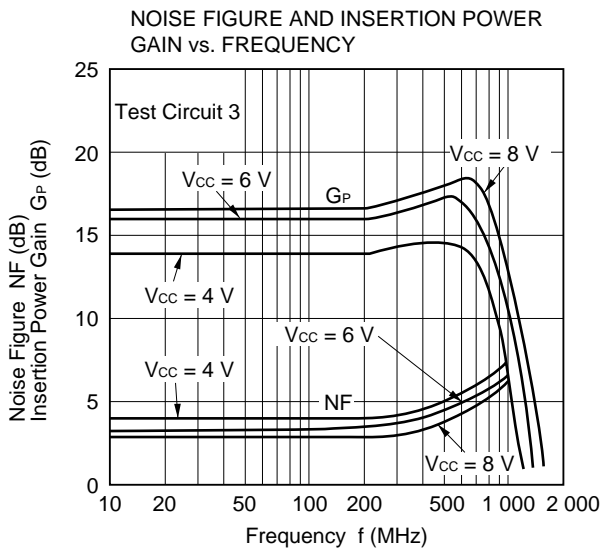
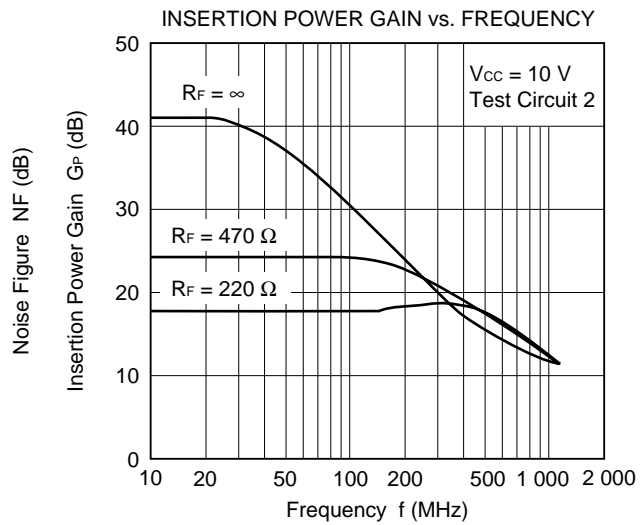
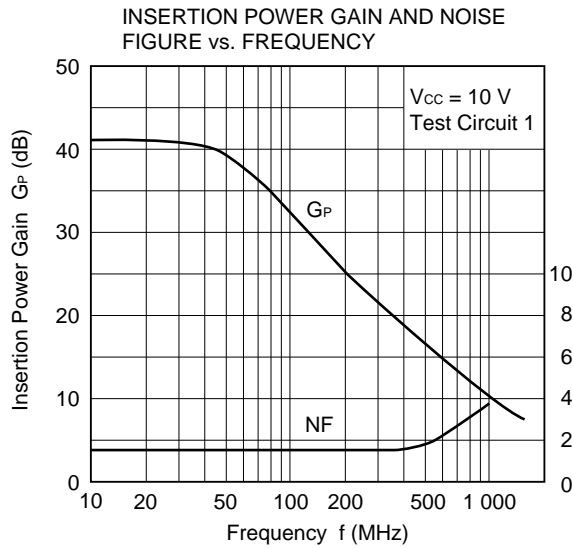
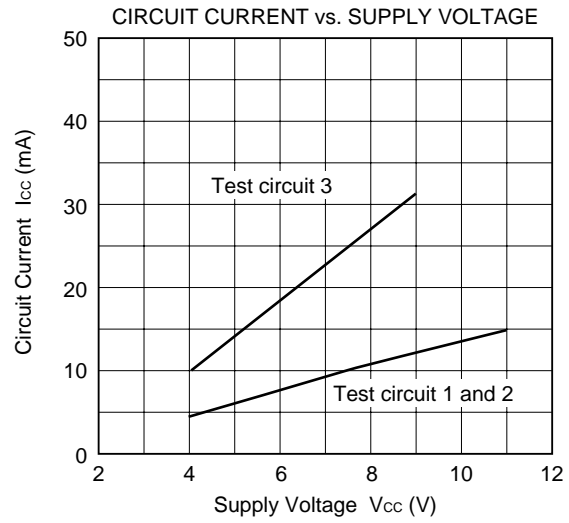
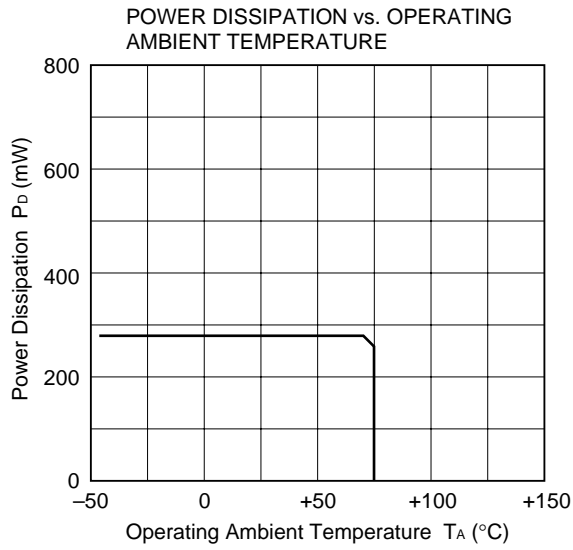
- Notes**
1. 50 × 50 × 0.4 mm double sided copper clad polyimide board.
 2. Back side: GND pattern
 3. Solder plated on pattern
 4. ○ ○ : Through holes

COMPONENT LIST

| | Value | Remarks |
|----------|----------------------|--|
| C1 to C3 | 0.01 μF | Necessary to all the test circuits |
| C4 | 0.1 μF | |
| R1 | Open ^{Note} | In the case of Low-noise Amplifier |
| | 180 Ω | In the case of Wideband Low-noise Amplifier with improved output level |

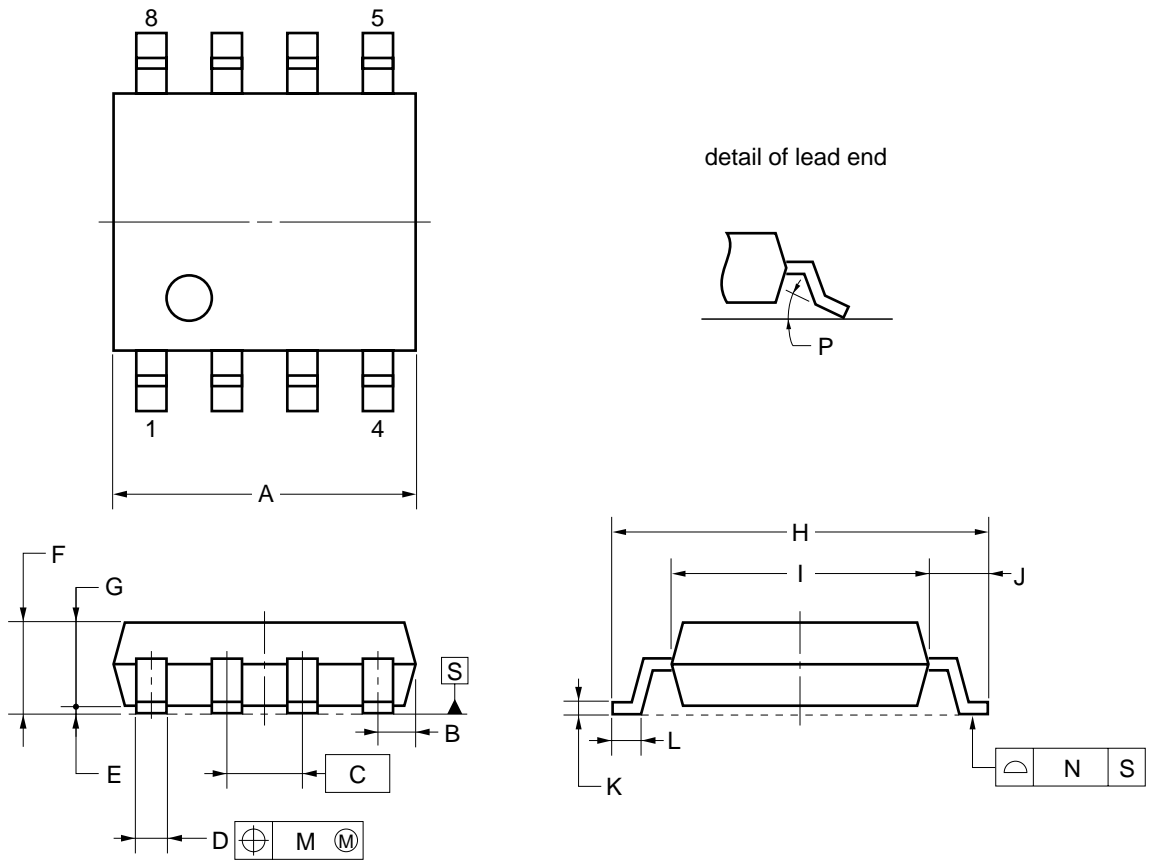
Note In the case of Low-noise Amplifier, R1 is not mounted.

TYPICAL CHARACTERISTICS (T_A = +25 °C, unless otherwise specified)



★ PACKAGE DIMENSIONS

8 PIN PLASTIC SOP (225 mil) (Unit: mm)



NOTE
 Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

| ITEM | MILLIMETERS |
|------|--|
| A | 5.2±0.2 |
| B | 0.85 MAX. |
| C | 1.27 (T.P.) |
| D | 0.42 ^{+0.08} _{-0.07} |
| E | 0.1±0.1 |
| F | 1.57±0.2 |
| G | 1.49 |
| H | 6.5±0.3 |
| I | 4.4±0.15 |
| J | 1.1±0.2 |
| K | 0.17 ^{+0.08} _{-0.07} |
| L | 0.6±0.2 |
| M | 0.12 |
| N | 0.10 |
| P | 3° ^{+7°} _{-3°} |

NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
- (3) Because the components will operate at high frequencies, apply chip capacitors and chip resistors with low parasitic inductance.
- (4) The DC capacitor must be attached to input pin and output pin.
- (5) The bypass capacitor should be attached to V_{cc} line.
- (6) In case of improved output level type application circuit, observe precaution not to exceed the power dissipation rating, especially in V_{cc} = 9 V or over.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

| Soldering Method | Soldering Conditions | Recommended Condition Symbol |
|------------------|---|------------------------------|
| Infrared Reflow | Package peak temperature: 235 °C or below Time: 30 seconds or less (at 210 °C) Count: 3, Exposure limit: None ^{Note} | IR35-00-3 |
| VPS | Package peak temperature: 215 °C or below Time: 40 seconds or less (at 200 °C) Count: 3, Exposure limit: None ^{Note} | VP15-00-3 |
| Wave Soldering | Soldering bath temperature: 260 °C or below Time: 10 seconds or less Count: 1, Exposure limit: None ^{Note} | WS60-00-1 |
| Partial Heating | Pin temperature: 300 °C Time: 3 seconds or less (per side of device) Exposure limit: None ^{Note} | — |

Note After opening the dry pack, keep it in a place below 25 °C and 65 % RH for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E).

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